Ordering number:EN3404A

DBF20T

Silicon Diffused Junction Type

2.0A Single-Phase Bridge Rectifier

Applications

· For primary rectification as switching regulator.

Features

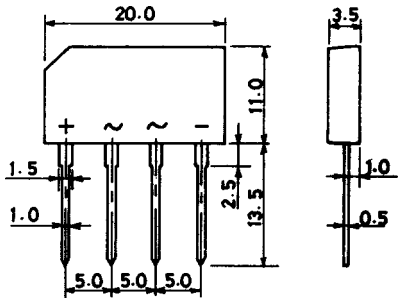
· High reliability attained glass passivation.
· High surge.
· Plastic molded structure.
· Peak reverse voltage:V_{RM}=200 to 600V.
· Average rectified current:I_O=2.0A.

Package Dimensions

unit:mm

1202

[DBF20T]



Specifications

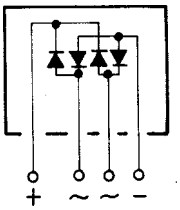
Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	DBF20TC	DBF20TE	DBF20TG	Unit
Peak Reverse Voltage	V_{RM}		200	400	600	V
Average Rectified Current	I_O	Tc=114˚C, with 50×50×1.5mm³ Al fin	→	→	2.0	A
		Ta=25˚C, without fin	→	→	1.5	A
Surge Forward Current	I_{FSM}	50Hz sine wave, 1 cycle	→	→	80	A
Junction Temperature	Tj		→	→	150	˚C
Storage Temperature	Tstg		→	→	–40 to +150	˚C

Electrical Characteristics at Ta = 25˚C, per constituent element of bridge.

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Forward Voltage	V_F	I_F=0.75A			1.05	V
Reverse Current	I_R	V_R:At each V_{RM}			10	μA
Thermal Resistance (Junction-Ambient)	Rth(j-a)	Without fin			50	˚C/W
Thermal Resistance (Junction-Case)	Rth(j-c)	With Al fin			10	˚C/W

Electrical Connection



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